

This listing of claims replaces all prior versions, and listings of claims in the instant application:

Listing of Claims:

1-21. (Canceled)

22. (Currently amended) A method comprising:

forming a first well of a first conductivity, a second well of said first conductivity, and a third well of a second conductivity in a front side of a bulk material;

forming a first buried layer of said second conductivity between a back side of said bulk material and said first well, said second well and said third well;

forming a second buried layer of said first conductivity between said first buried layer and said second ~~well~~, well;

supplying a first potential to said first well;

supplying a second potential to said second well with said second buried layer; and

supplying a third potential to said third well with said first buried layer.

23. (Original) The method of Claim 22 further comprising electrically isolating said first potential from said second potential with said third well and said first buried layer.

24. (New) The method of Claim 22 further comprising electrically connecting said first well to said bulk material through an opening in said first buried layer.

25. (New) The method of Claim 24 wherein said first potential is supplied to said bulk material and thereby to said first well.

26. (New) The method of Claim 24 wherein said opening is of said first conductivity.

27. (New) The method of Claim 22 further comprising:  
forming a fourth well of said second conductivity in said front side of a bulk material, said second buried layer being between said first buried layer and said fourth well; and  
electrically connecting said fourth well to said first buried layer through an opening in said second buried layer.

28. (New) The method of Claim 27 wherein said opening is of said second conductivity.

29. (New) The method of Claim 22 further comprising:  
forming a fourth well of said second conductivity and a fifth well of said first conductivity in said front side of a bulk material, said second buried layer being between said first buried layer and said fourth well and said fifth well;  
forming a third buried layer between said second buried layer and said fourth well and said fifth well; and  
electrically connecting said fifth well to said second buried layer through an opening in said third buried layer.

30. (New) The method of Claim 29 wherein said third buried layer is of said second conductivity and wherein said opening is of said first conductivity.

31. (New) The method of Claim 29 further comprising supplying said first potential to said third buried layer and said fourth well.

32. (New) The method of Claim 29 further comprising electrically isolating said first potential supplied to said

third buried layer and said fourth well from said third potential with said second well and said second buried layer.

33. (New) The method of Claim 22 wherein said bulk material is of said first conductivity.

34. (NEW) A method comprising:  
supplying a first potential to a back side of a bulk material of a first conductivity;  
forming first wells of said first conductivity in a front side of said bulk material;  
supplying at least one of said first wells with said first potential;  
forming second wells of said first conductivity in said front side of said bulk material;  
supplying at least one of said second wells with a second potential which is different than said first potential;  
forming third wells of a second conductivity in said front side of said bulk material; and  
forming a first buried layer of said second conductivity extending between said back side of said bulk material and said first, second and third wells;  
forming at least one opening in said first buried layer to electrically connect said bulk material with said at least one of said first wells supplied with said first potential;  
electrically isolating said at least one of said second wells supplied with said second potential from said at least one opening of said first buried layer by at least one of said third wells.

35. (New) The method of Claim 34, wherein said first potential is a ground potential, and said second potential is a bias potential.

36. (New) The method of Claim 34, further comprising forming a second buried layer of said first conductivity extending between said first buried layer of said second conductivity and said at least one of said second wells supplied with said second potential; and

routing said second potential to said at least one of said second wells with said second buried layer.

37. (New) The method of Claim 34, further comprising routing a bias potential to said at least one of said third wells with said first buried layer.

38. (New) A method comprising:  
forming p-wells in a front side of a bulk material;  
forming n-wells in said front side of said bulk material;  
and

forming n layers and p layers alternately within said bulk material between a back side of said bulk material and said n-wells and p-wells;

wherein said n layers are electrically isolated from one another and respectively route different potentials to selected ones of said n-wells, and wherein said p layers are electrically isolated from one another and respectively route different potentials to selected ones of said p-wells.